

/ Descriptions

TO-252 SiC

SiC Schottky Barrier Diode in a TO-252 Plastic Package.

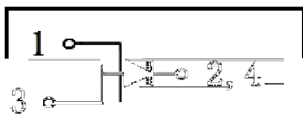
/ Features

Low power loss, high efficiency, HF Product.

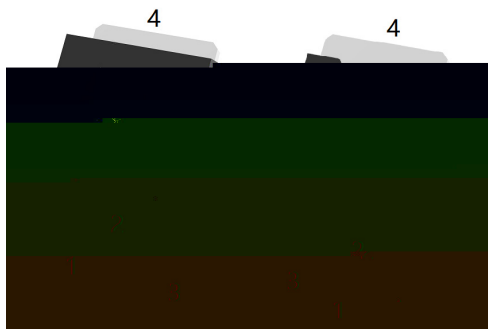
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode

/ Equivalent Circuit



/ Pinning



PIN1 3 Anode PIN 2 4 Cathode

/ Marking

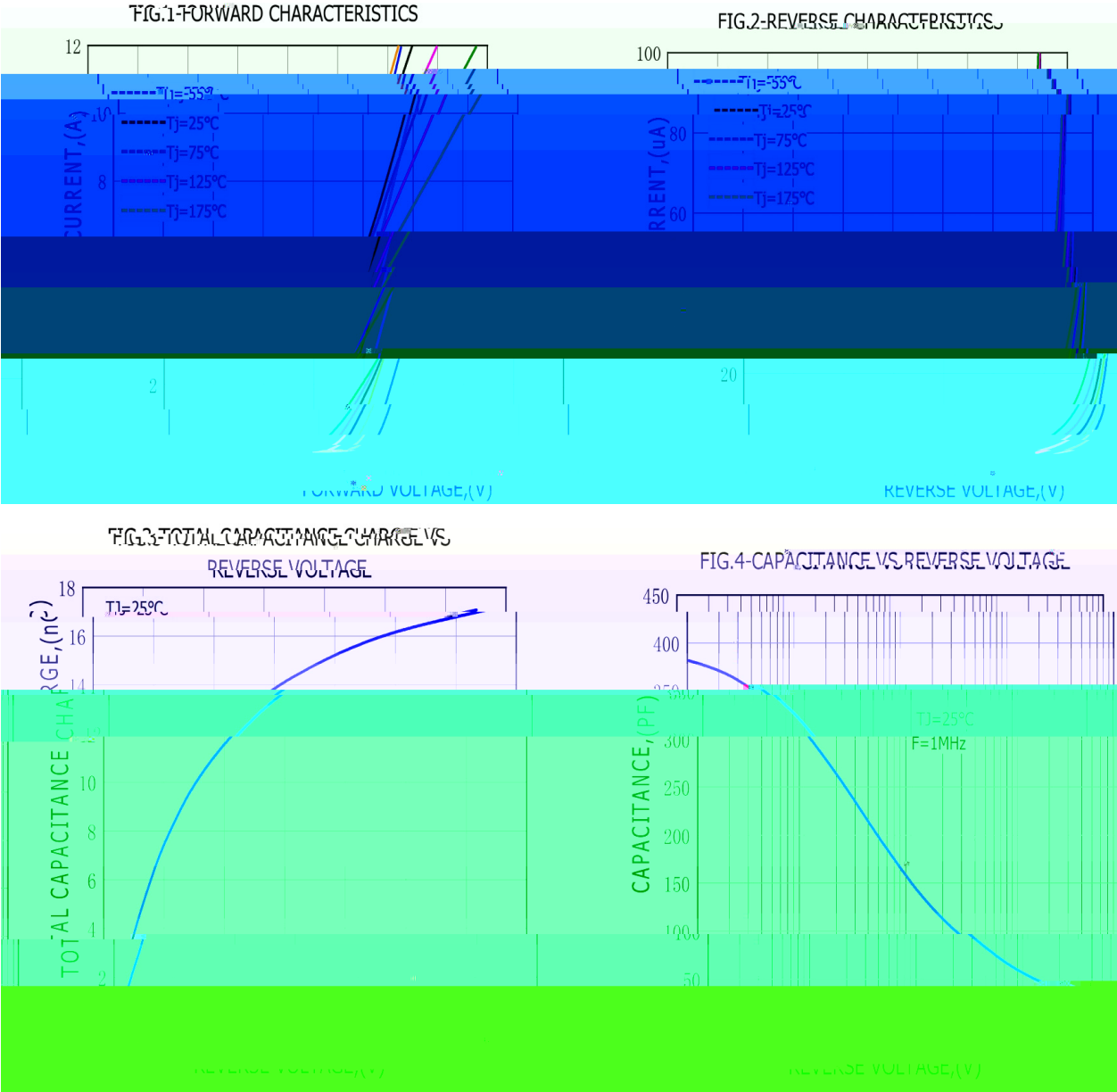
See Marking Instructions.



Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	650	V
Maximum RMS Voltage	V_{RMS}	455	V
Maximum DC blocking Voltage	V_{DC}	650	V
Continuous Forward Current, $T_C=150$	I_F	6	A
Peak forward surge current, $t_p=8.3ms$	I_{FSM}	52	A
Total power dissipation	P_D	53	W
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	2.8	/W
Operation Junction Temperature and Storage Temperature	T_J, T_{STG}	-55~+175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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/ Electrical Characteristic Curve



/ Package Dimensions



单位: mm

Max	Symbol	Min	Max	Symbol	Min
6.25	A	2.30	2.40	F	5.95
1.6	B	0.50	0.62	L	4.43
1.61	C	0.45	1.1	E	9.45
0.66	D	0.55	0.62	K	0.60
0.66	E	0.55	0.62	L	4.43
0.66	F	0.55	0.62	M	0.60
0.66	G	0.55	0.62	N	0.60
0.66	H	0.55	0.62	O	0.60
0.66	I	0.55	0.62	P	0.60
0.66	J	0.55	0.62	Q	0.60
0.66	K	0.55	0.62	R	0.60
0.66	L	0.55	0.62	S	0.60
0.66	M	0.55	0.62	T	0.60
0.66	N	0.55	0.62	U	0.60
0.66	O	0.55	0.62	V	0.60
0.66	P	0.55	0.62	W	0.60
0.66	Q	0.55	0.62	X	0.60
0.66	R	0.55	0.62	Y	0.60
0.66	S	0.55	0.62	Z	0.60

11-252

